

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	1	((silicon or si) near2 (wafer or substrate) and (oxygen near precipitat\$4 or bmd or oxygen near agglomerat\$4) near6 (size or radius or diameter) and (oxygen or o) near2 (density or concentration) and (carbon or c) near2 (density or concentration)).clm.	US-PGPUB	OR	ON	2008/03/24 15:43
L4	1	((silicon or si) near2 (wafer or substrate) and (seco near etch \$4)).clm.	US-PGPUB	OR	ON	2008/03/24 15:45
L5	12	((silicon or si) near2 (wafer or substrate) and (oxygen near precipitat\$4 or bmd or oxygen near agglomerat\$4 or oxygen near4 nucleus) near4 (heat\$4 or thermal\$4 or rta or anneal\$4) and (oxygen or o) near2 (density or concentration) and (carbon or c) near2 (density or concentration)).clm.	US-PGPUB	OR	ON	2008/03/24 15:46
L6	4	((silicon or si) near2 (wafer or substrate) and (bmd or grown adj2 defect) and (oxygen or o) near2 (density or concentration) and (carbon or c) near2 (density or concentration)).clm.	US-PGPUB	OR	ON	2008/03/24 15:46

L7	10	((silicon or si) near2 (wafer or substrate) and (astm) and (oxygen or o) near2 (density or concentration) and (carbon or c) near2 (density or concentration)).clm.	US-PGPUB	OR	ON	2008/03/24 15:47
L9	55	257/E29.068.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/24 15:54
L10	326	257/E29.109.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/24 15:58
L11	648	257/E21.318.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/24 16:00
S36	264	438/799.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/18 09:18
S37	161	257/610.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/18 09:28
S38	151	257/611.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/18 09:33
S39	138	257/612.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/18 09:38

S40	530	257/655.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/18 09:42
S41	568	117/2.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/18 10:11
S42	493	117/3.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/18 10:51
S43	276	117/14.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 09:25
S44	68	(large or high) near (resistance or resistivity) near4 (silicon or si) near (substrate or wafer) and (bmd or oxygen near2 precipitat\$3 or bulk adj microdefect or bulk adj micro adj defect)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 09:38
S45	28	(large or high) near (resistance or resistivity) near4 (silicon or si) near (substrate or wafer) and (oxygen) near4 (density or concentration) and (carbon) near4 (density or concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 09:43

S46	21	(rf or radio adj frequency or high adj frequency or microwave) near4 (silicon or si) near (substrate or wafer) and (bmd or oxygen near2 precipitat\$3 or bulk adj microdefect or bulk adj micro adj defect)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 09:46
S47	29	(rf or radio adj frequency or high adj frequency or microwave) near4 (silicon or si) near (substrate or wafer) and carbon near2 (concentration or density)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 09:47
S48	59	oxygen adj concentration near4 astm	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 10:00
S49	544	(silicon or si) near2 (wafer or substrate) and (oxygen near precipitate or bmd or oxygen near agglomerat\$4) near6 (density or concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/24 09:21
S50	321	(silicon or si) near2 (wafer or substrate) and (oxygen near precipitate or bmd or oxygen near agglomerat\$4) and (carbon or c) near3 (density or concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/24 10:35

S51	260	(silicon or si) near2 (wafer or substrate) and (oxygen near precipitate or bmd or oxygen near agglomerat\$4) and (oxygen or o! or "o. sub.2") near3 (density or concentration) and (carbon or c) near3 (density or concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/24 10:59
S52	58	(silicon or si) near2 (wafer or substrate) and (oxygen near precipitate or bmd or oxygen near agglomerat\$4) near4 (size or radius or diameter) and (oxygen or o! or "o.sub.2") near3 (density or concentration) and (carbon or c) near3 (density or concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/24 11:00

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